

## High-speed Switching Transistor ( $-60V$ , $-12A$ )

2SA1870

### Features

- 1) High speed switching, typically  $t_f=0.17\ \mu s$  at  $I_c=-6A$ .
- 2) Low saturation voltage, typically  $V_{CE(sat)}=-0.2V$  at  $I_c / I_s=-6A / -0.3A$ .
- 3) Wide SOA (safe operating area)

### Packaging specifications and $h_{FE}$

Type	2SA1870
Package	PSD3
$h_{FE}$	EF
Code	TL
Basic ordering unit (pieces)	1000

### Absolute maximum ratings ( $T_a=25^\circ C$ )

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	-100	V
Collector-emitter voltage	$V_{CEO}$	-60	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-12	A
		-20	A (Pulse) *
Collector power dissipation	$P_C$	1.5	W
		35	W ( $T_C=25^\circ C$ )
Junction temperature	$T_J$	150	$^\circ C$
Storage temperature	$T_{STG}$	-55~+150	$^\circ C$

\* Single pulse,  $P_w=100ms$

### Electrical characteristics ( $T_a=25^\circ C$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	-100	—	—	V	$I_C=-50\ \mu A$
Collector-emitter breakdown voltage	$BV_{CEO(SUS)}$	-60	—	—	V	$I_C=-6A, I_S=-0.6A, L=1mH$
Collector-emitter breakdown voltage	$BV_{CEO}$	-60	—	—	V	$I_C=-1mA$
Emitter-base breakdown voltage	$BV_{EBO}$	-5	—	—	V	$I_E=-50\ \mu A$
Collector cutoff current	$I_{CBO}$	—	—	-10	$\mu A$	$V_{CB}=-100V$
Emitter cutoff current	$I_{EBO}$	—	—	-10	$\mu A$	$V_{CB}=-5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	-0.2	-0.3	V	$I_C/I_S=-6A/-0.3A$
		—	—	-0.5	V	$I_C/I_S=-8A/-0.4A$
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	-1.2	V	$I_C/I_S=-6A/-0.3A$
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	-1.5	V	$I_C/I_S=-8A/-0.4A$
DC current transfer ratio	$h_{FE}$	100	—	320	—	$V_{CE}=-2V, I_C=-2A$
Transition frequency	$f_T$	—	80	—	MHz	$V_{CE}=-10V, I_E=-1A, f=30MHz$
Output capacitance	$C_{OB}$	—	250	—	pF	$V_{CE}=-10V, I_E=0A, f=1MHz$
Turn-on time	$t_{on}$	—	—	0.3	$\mu s$	$I_C=-6A$
Storage time	$t_{stg}$	—	—	1.5	$\mu s$	$I_{B1}=-I_{B2}=-0.3A$
Fall time	$t_f$	—	0.17	0.3	$\mu s$	$V_{CC}=-30V$

(96-113-A325)